



HFZT

1N4448WS

FAST SWITCHING DIODE

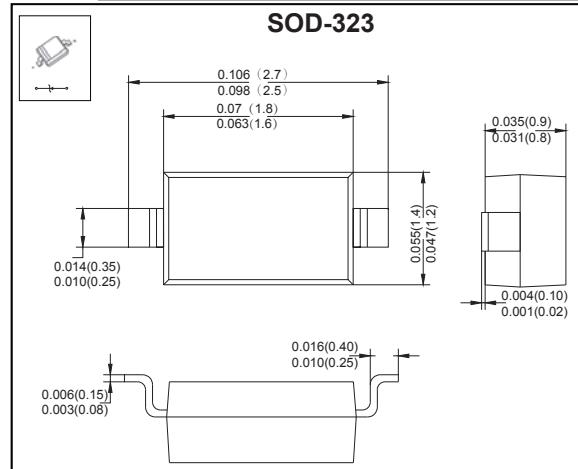
VOLTAGE RANGE: 100V
PEAK PULSE POWER: 200mW

FEATURES

- Small Package
- Low Reverse Current
- Fast Switching Speed
- Surface Mount Package Ideally Suited for Automatic Insertion

MECHANICAL DATA

- Case: SOD-323 Small Outline Plastic Package
- Polarity: Color band denotes cathode end
- Mounting Position: Any



MAXIMUM RATINGS AND CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified

Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Peak Repetitive Peak Reverse Voltage	V_{RRM}		
Working Peak Reverse Voltage	V_{RWM}	75	V
DC Blocking Voltage	V_R		
RMS Reverse Voltage	$V_{R(RMS)}$	53	V
Forward Continuous Current	I_{FM}	500	mA
Average Rectified Output Current	I_o	250	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}	2.0	A
Power Dissipation	P_d	200	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	625	°C/W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{STG}	-55~+150	°C

Electrical Specification (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse Breakdown Voltage	$V_{(BR)R}$	75			V	$I_R=10\mu A$
Forward Voltage	V_{F1}	0.62		0.72	V	$I_F=5mA$
	V_{F2}			0.855	V	$I_F=10mA$
	V_{F3}			1.0	V	$I_F=100mA$
	V_{F4}			1.25	V	$I_F=150mA$
Reverse Current	I_{R1}			2.5	μA	$V_R=75V$
	I_{R2}			25	nA	$V_R=20V$
Capacitance Between Terminals	C_T			4	pF	$V_R=0V, f=1MHz$
Reverse Recovery Time	t_{rr}			4	ns	$I_F=I_R=10mA$ $I_{rr}=0.1 \times I_R, R_L=100\Omega$

RATINGS AND CHARACTERISTIC CURVES

Typical Characteristics

